Data sheet

Bookham TECHNOLOGY

Engineering Datasheet

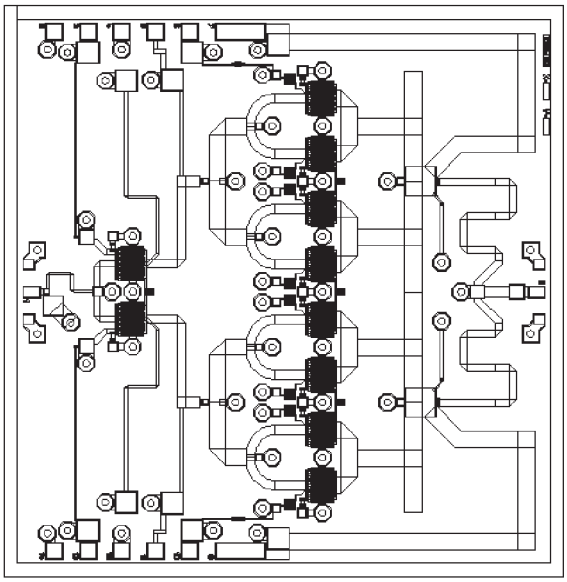
8.5 – 10.5GHz Power Amplifier

Features

- 15dB Gain Typical
- P-1dB; 37dBm typical @ 9.5GHz

The **P35-5130-000-200** is a high performance 8.5-10.5GHz Gallium Arsenide power amplifier, capable of output powers of 5 Watts.

The die is fabricated using Caswell Technology's 0.20µm gate length, pHEMT process and is fully protected using Silicon Nitride passivation for excellent performance and reliability.



Electrical Performance

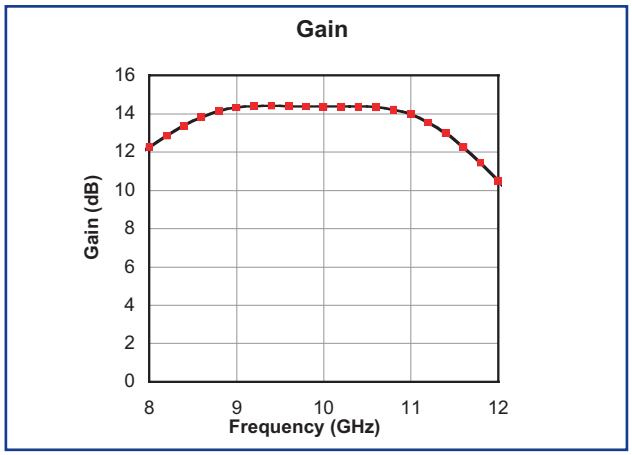
Ambient Temperature 22±3°C, Zo = 50Ω, Vd1 = 5V, Vd2=7V, Vgg Set for Typical Drain Currents. Unless otherwise stated

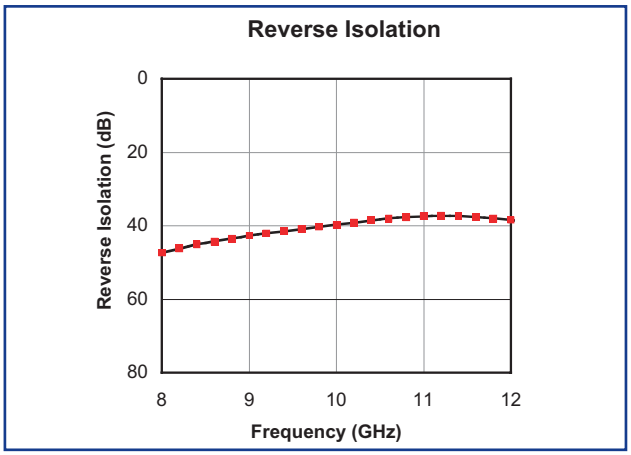
Parameter	Conditions	Min	Typ	Max	Units
Small Signal Gain	8.5 – 10.5GHz	-	15	-	dB
Gain Flatness	8.5 – 10.5GHz	-	±0.5	-	dB
Input Return Loss	8.5 – 10.5GHz	-	8	-	dB
Output Return Loss	8.5 – 10.5GHz	-	8	-	dB
P-1dB Output Power	9.5 GHz	-	37	-	dBm
PAE	9.5 GHz	-	25	-	%
Gate Voltage Vgg	-	-	-0.6	-	Volts
First Stage Current	Vd = 5V	-	600	-	mA
Second Stage Current	Vd = 7V	-	2400	-	mA

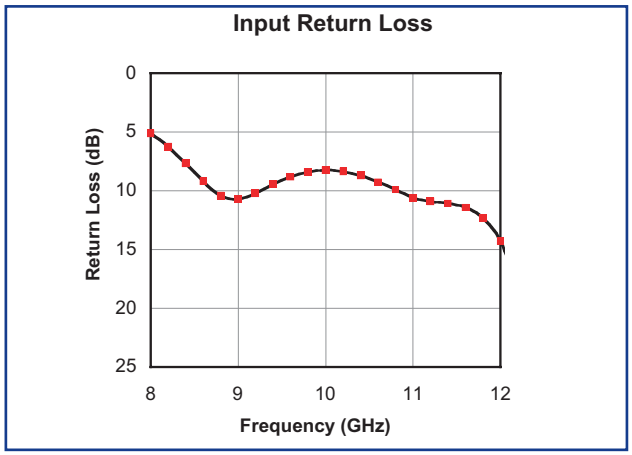
Notes

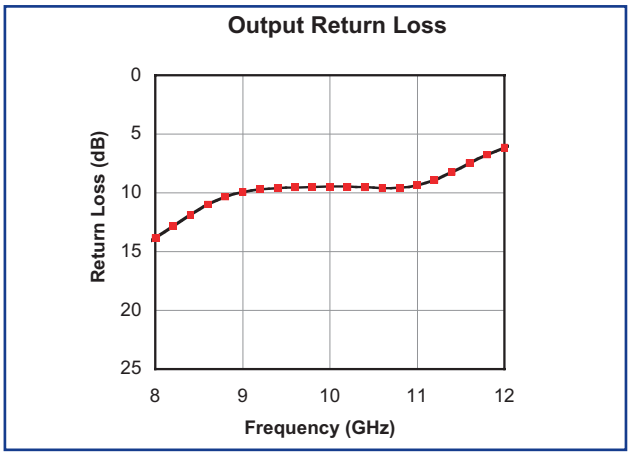
1. All parameters measured on wafer

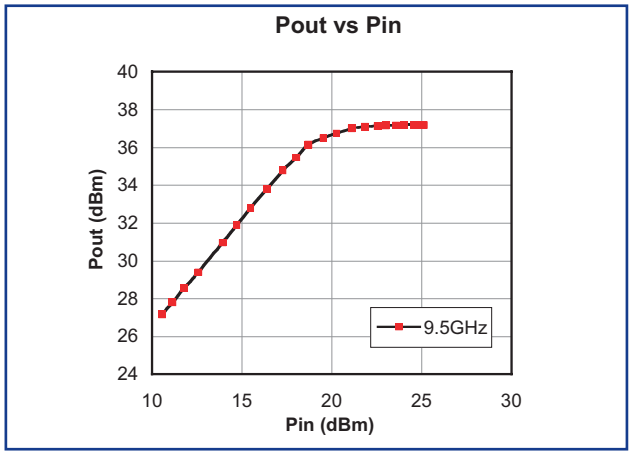
Preliminary RFOW Performance



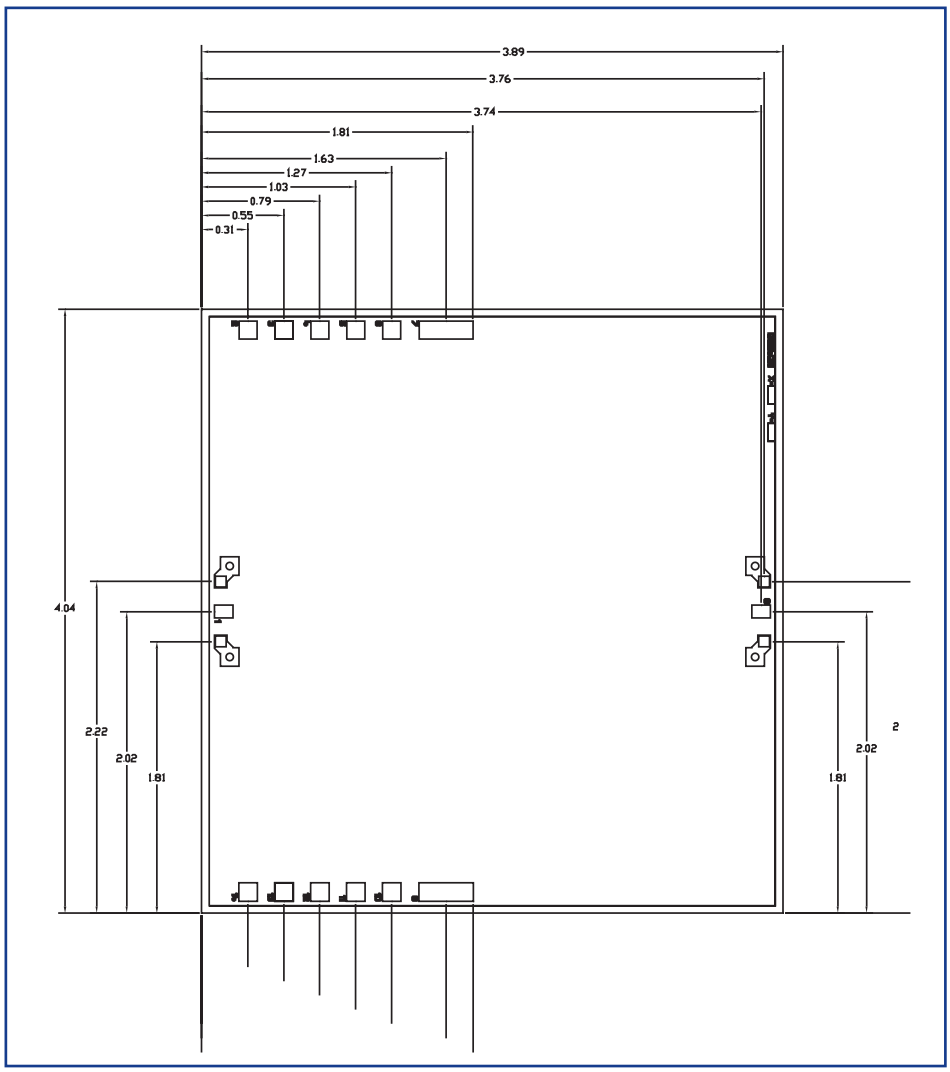








Chip Outline



Bookham TECHNOLOGY
Thinking RF solutions

MMICS

Bookham Technology plc
Caswell
Towcester
Northamptonshire
NN12 8EQ
UK

- **Tel: +44 (0) 1327 356 789**
- **Fax: +44 (0) 1327 356 698**

rfsales@bookham.com

Important Notice

Bookham Technology has a policy of continuous improvement. As a result certain parameters detailed on this flyer may be subject to change without notice. If you are interested in a particular product please request the product specification sheet, available from any RF sales representative.

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Pad Details

Pad	Function
1	RF Input
2	Gnd
3	Vg1
4	Gnd
5	Vd1
6	Vg2
7	Vd2
8	RF Output
9	Vd2
10	Vg2
11	Vd1
12	Gnd
13	Vg1
14	Gnd

Ordering Information

P35-5130-000-200

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